

关键参数 Key Parameters

V_{CES}		750	V
$V_{CE(sat)}$	Typ.	1.25	V
I_C	Max.	820	A
$I_{C(RM)}$	Max.	1640	A

典型应用 Typical Applications

● 电动汽车	Automotive Applications
● 混合动力/纯电动车	Hybrid/Electrical Vehicles
● 电机驱动	Motor Drives

特点 Features

● 铜针翅基板	Cu pin-fin Baseplate
● 低开关损耗	Low Switching Losses
● 750V 额定电压	Blocking Voltage 750V
● 低感设计	Low Inductive Design

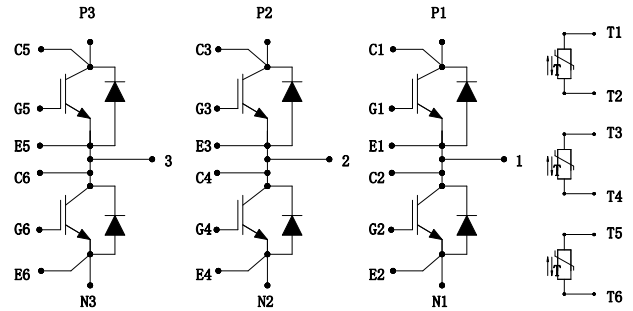
电路结构 Circuit Configuration


图 1. 电路结构

Fig. 1 Circuit configuration

模块外形 Module Appearance


图 2. 模块外形

Fig. 2 Module appearance

模块标签说明

Module Label Code Instruction

数据位置 Data position	数据内容 Content of data
1--8	模块批次号 Module batch number
9--12	模块序列号 Module serial number

最大额定值
Absolute Maximum Ratings

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	数值 Value	单位 Unit
V_{CES}	集电极-发射极电压 Collector-emitter voltage	$V_{GE} = 0V, T_C = 25\text{ }^\circ\text{C}$	750	V
V_{GES}	栅极-发射极电压 Gate-emitter voltage	$T_C = 25\text{ }^\circ\text{C}$	± 20	V
I_C	集电极电流 Collector-emitter current	$T_F = 80\text{ }^\circ\text{C}, T_{vjmax} = 175\text{ }^\circ\text{C}$	450	A
	额定电流 Rating Current		820	A
$I_{C(RM)}$	集电极峰值电流 Peak collector current	$t_p = 1\text{ms}$	1640	A
P_{max}	晶体管部分最大损耗 Max. transistor power dissipation	$T_{vj} = 175\text{ }^\circ\text{C}, T_C = 25\text{ }^\circ\text{C}$	1111	W
ρ_t	二极管 ρ_t 值 Diode ρ_t	$V_R = 0V, t_p = 10\text{ms}, T_{vj} = 150\text{ }^\circ\text{C}$	14.4	kA^2s
V_{isol}	绝缘电压(模块) Isolation voltage – per module	短接所有端子，端子与基板间施加电压 (Commoned terminals to baseplate), AC RMS, 1 min, 50Hz, $T_C = 25\text{ }^\circ\text{C}$	2500	V

热和机械数据
Thermal & Mechanical Data

参数 Symbol	说明 Explanation	值 Value	单位 Unit
爬电距离 Creepage distance	端子-散热器 Terminal to heatsink	9	mm
	端子-端子 Terminal to terminal	9	mm
绝缘间隙 Clearance	端子-散热器 Terminal to heatsink	4.5	mm
	端子-端子 Terminal to terminal	4.5	mm
相对漏电起痕指数 CTI (Comparative tracking index)		>200	

热和机械数据
Thermal & Mechanical Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$R_{th(J-F)}$ IGBT	IGBT 热阻 Thermal resistance – IGBT	冷却液: 50%乙二醇溶液; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 75 \text{ }^\circ\text{C}$ Cooling Fluid: 50% water / 50% ethylenglycol; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 75 \text{ }^\circ\text{C}$		115	135	K / kW
$R_{th(J-F)}$ Diode	二极管热阻 Thermal resistance – Diode	冷却液: 50%乙二醇溶液; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 75 \text{ }^\circ\text{C}$ Cooling Fluid: 50% water / 50% ethylenglycol; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 75 \text{ }^\circ\text{C}$		160	180	K / kW
ΔP	冷却液流阻 Pressure drop in cooling circuit	冷却液: 50%乙二醇溶液; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 25 \text{ }^\circ\text{C}$ Cooling Fluid: 50% water / 50% ethylenglycol; $\Delta V/\Delta t=10 \text{ dm}^3/\text{min}$; $T_F = 25 \text{ }^\circ\text{C}$		68		mbar
P	冷却液最大压力 Maximum pressure in cooling circuit				2	bar
$T_{vj op}$	工作结温 Operating junction temperature	IGBT 部分 (IGBT)	-40 150		150 175	$^\circ\text{C}$
		二极管部分 (Diode)	-40 150		150 175	$^\circ\text{C}$
T_{stg}	存储温度 Storage temperature range		-40		125	$^\circ\text{C}$
M	安装力矩 Screw torque	安装紧固用 - M4 Mounting - M4	1.8	2.0	2.2	Nm
		PCB 安装用 PCB Mounting	0.55	0.6	0.65	Nm

热敏电阻数据
NTC-Thermistor Data

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
R_{25}	额定电阻值 Rated resistance	$T_C = 25 \text{ }^\circ\text{C}$		5		k Ω
$\Delta R/R$	R_{100} 偏差 Deviation of R_{100}	$T_C = 100 \text{ }^\circ\text{C}$, $R_{100}=493\Omega$	-5		5	%
P_{25}	耗散功率 Power dissipation	$T_C = 25 \text{ }^\circ\text{C}$			20	mW
$B_{25/50}$	B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$		3375		K
$B_{25/80}$	B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298.15 \text{ K}))]$		3411		K
$B_{25/100}$	B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298.15 \text{ K}))]$		3433		K

电特性值
Electrical Characteristics

 除非特别声明，否则 $T_C = 25\text{ }^\circ\text{C}$
 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
I_{CES}	集电极截止电流 Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 150\text{ }^\circ\text{C}$			10	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_C = 175\text{ }^\circ\text{C}$			15	mA
I_{GES}	栅极漏电流 Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			0.5	μA
$V_{GE(TH)}$	栅极-发射极阈值电压 Gate threshold voltage	$I_C = 15\text{mA}, V_{GE} = V_{CE}$	5.30	5.90	6.50	V
$V_{CE(sat)}^{(*1)}$	集电极-发射极饱和电压 Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 450A$		1.25	1.55	V
		$V_{GE} = 15V, I_C = 450A, T_{vj} = 150\text{ }^\circ\text{C}$		1.30		V
		$V_{GE} = 15V, I_C = 450A, T_{vj} = 175\text{ }^\circ\text{C}$		1.30		V
		$V_{GE} = 15V, I_C = 820A$		1.60		V
I_F	二极管正向直流电流 Diode forward current	DC		450		A
	二极管额定正向电流 Diode rating forward current			820		A
I_{FRM}	二极管正向重复峰值电流 Diode peak forward current	$t_p = 1\text{ms}$		1640		A
$V_F^{(*1)}$	二极管正向电压 Diode forward voltage	$I_F = 450A, V_{GE} = 0$		1.65	1.95	V
		$I_F = 450A, V_{GE} = 0, T_{vj} = 150\text{ }^\circ\text{C}$		1.65		V
		$I_F = 450A, V_{GE} = 0, T_{vj} = 175\text{ }^\circ\text{C}$		1.65		V
		$I_F = 820A, V_{GE} = 0$		2.05		V
I_{SC}	短路电流 Short circuit current	$T_{vj} = 150\text{ }^\circ\text{C}, V_{CC} = 400V,$ $V_{GE} \leq 15V, t_p \leq 6\mu\text{s},$ $V_{CE(max)} = V_{CES} - L^{(*2)} \times di/dt,$ IEC 6074-9		3800		A

注意: 1.(*1) 表示该参数的测试点为辅助母排端子 (*1) indicates it is measured at the auxiliary busbar terminal),

Note: 2.(*2) 表示 L 是电路杂散电感加上 L_M (*2) indicates L is the circuit stray inductance plus L_M).

电特性值
Electrical Characteristics

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 $T_C = 25\text{ }^\circ\text{C}$ unless otherwise stated

符号 Symbol	参数名称 Parameter	条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
C_{ies}	输入电容 Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		74		nF
Q_g	栅极电荷 Gate charge	$\pm 15V$		4.20		μC
C_{res}	反向传输电容 Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$		0.29		nF
L_M	模块电感 Module inductance			8		nH
R_{INT}	内阻 Internal transistor resistance			0.5		m Ω

电特性值
Electrical Characteristics

符号 Symbol	参数名称 Parameter	测试条件 Test Conditions	最小值 Min.	典型值 Typ.	最大值 Max.	单位 Unit
$t_{d(off)}$	关断延迟时间 Turn-off delay time	$I_C = 450A,$ $V_{CE} = 400V,$ $V_{GE} = \pm 15V,$ $R_{G(OFF)} = 5.1\Omega,$ $L_S = 55nH,$ $dv/dt = 4400V/us$ ($T_{vj} = 150^\circ C$).	$T_{vj} = 25^\circ C$		1065	ns
			$T_{vj} = 150^\circ C$		1080	
			$T_{vj} = 175^\circ C$		1095	
t_f	下降时间 Fall time		$T_{vj} = 25^\circ C$		80	ns
			$T_{vj} = 150^\circ C$		85	
			$T_{vj} = 175^\circ C$		90	
E_{OFF}	关断损耗 Turn-off energy loss		$T_{vj} = 25^\circ C$		33	mJ
			$T_{vj} = 150^\circ C$		36	
			$T_{vj} = 175^\circ C$		37	
$t_{d(on)}$	开通延迟时间 Turn-on delay time	$T_{vj} = 25^\circ C$		845	ns	
		$T_{vj} = 150^\circ C$		850		
		$T_{vj} = 175^\circ C$		855		
t_r	上升时间 Rise time	$T_{vj} = 25^\circ C$		87	ns	
		$T_{vj} = 150^\circ C$		105		
		$T_{vj} = 175^\circ C$		105		
E_{ON}	开通损耗 Turn-on energy loss	$T_{vj} = 25^\circ C$		10.0	mJ	
		$T_{vj} = 150^\circ C$		10.5		
		$T_{vj} = 175^\circ C$		11.0		
Q_{rr}	二极管反向恢复电荷 Diode reverse recovery charge	$T_{vj} = 25^\circ C$		47	μC	
		$T_{vj} = 150^\circ C$		52		
		$T_{vj} = 175^\circ C$		57		
I_{rr}	二极管反向恢复电流 Diode reverse recovery current	$T_{vj} = 25^\circ C$		320	A	
		$T_{vj} = 150^\circ C$		335		
		$T_{vj} = 175^\circ C$		345		
E_{rec}	二极管反向恢复损耗 Diode reverse recovery energy	$T_{vj} = 25^\circ C$		15.5	mJ	
		$T_{vj} = 150^\circ C$		17.0		
		$T_{vj} = 175^\circ C$		18.5		

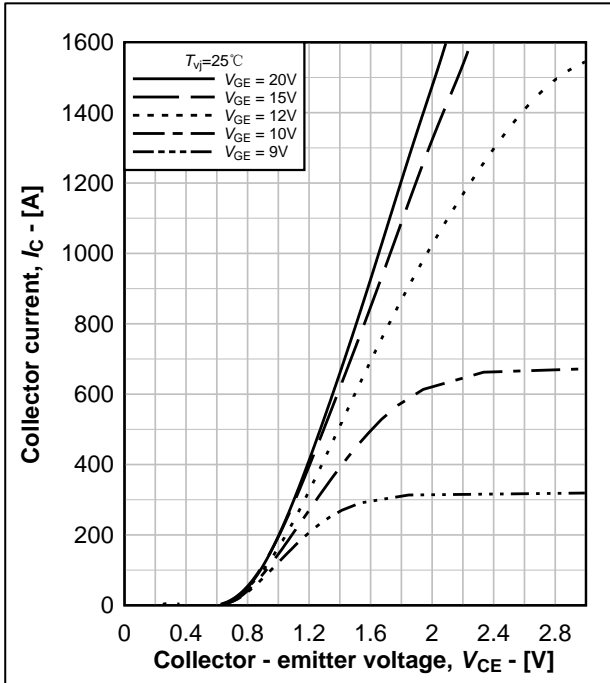


图 3. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.3 Typical IGBT output characteristics, $I_C = f(V_{CE})$

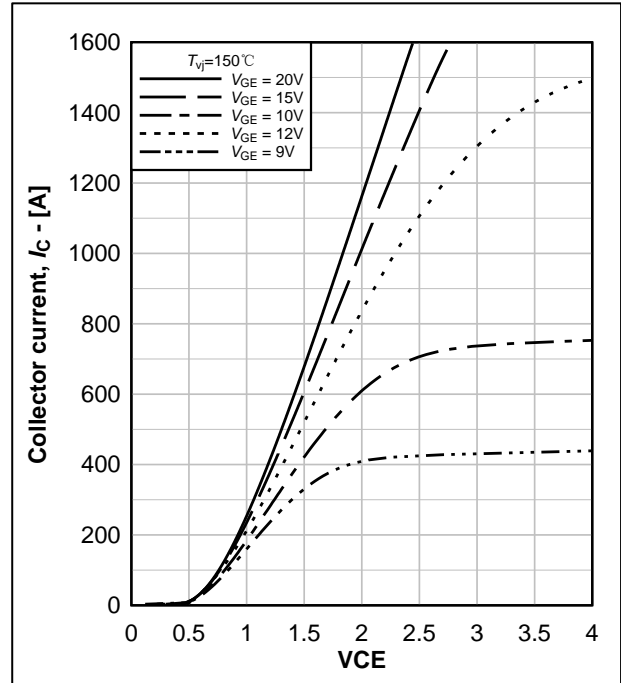


图 4. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.4 Typical IGBT output characteristics, $I_C = f(V_{CE})$

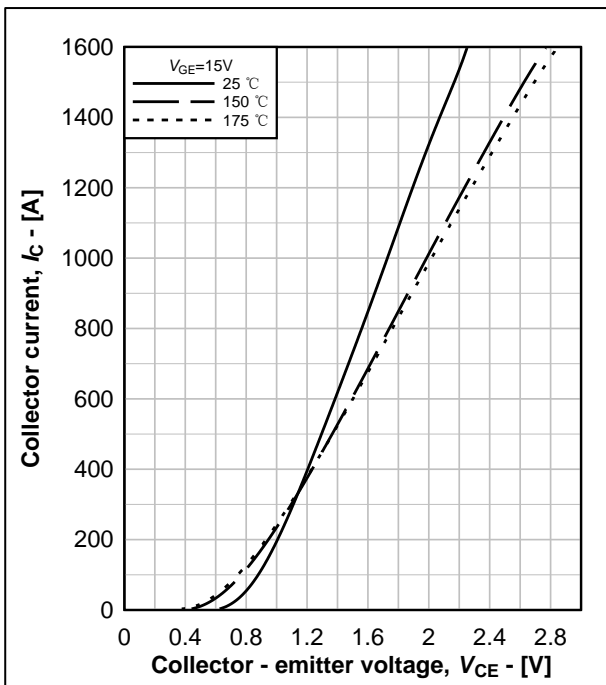


图 5. IGBT 输出特性典型曲线, $I_C = f(V_{CE})$

Fig.5 Typical IGBT output characteristics, $I_C = f(V_{CE})$

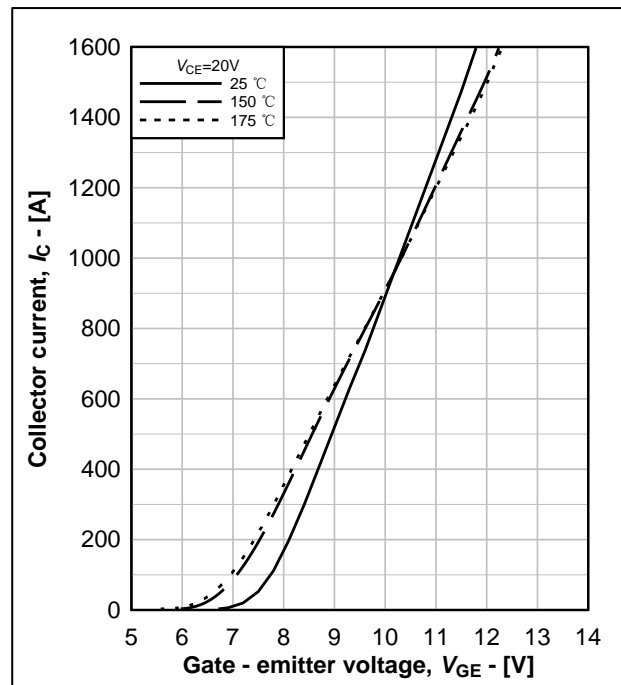


图 6. IGBT 传输特性典型曲线, $I_C = f(V_{GE})$

Fig.6 Typical IGBT transfer characteristics, $I_C = f(V_{GE})$

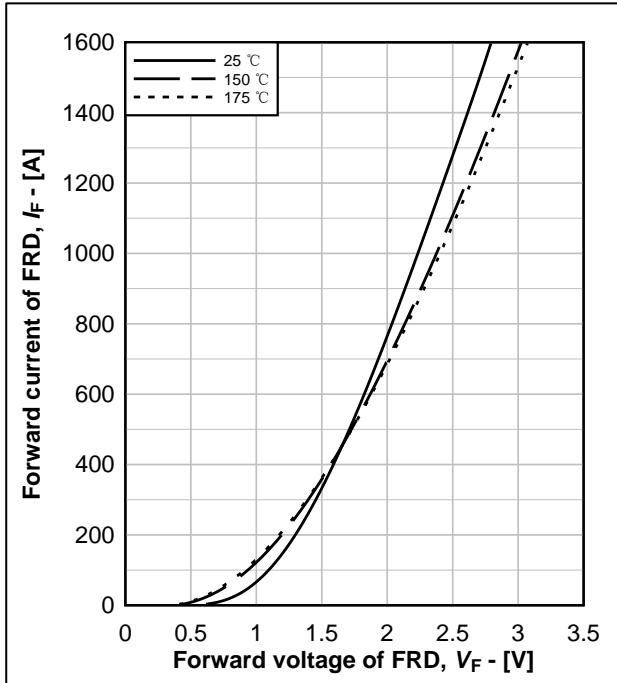


图 7. FRD 输出特性典型曲线, $I_F = f(V_F)$

Fig.7 Typical FRD output characteristics, $I_F = f(V_F)$

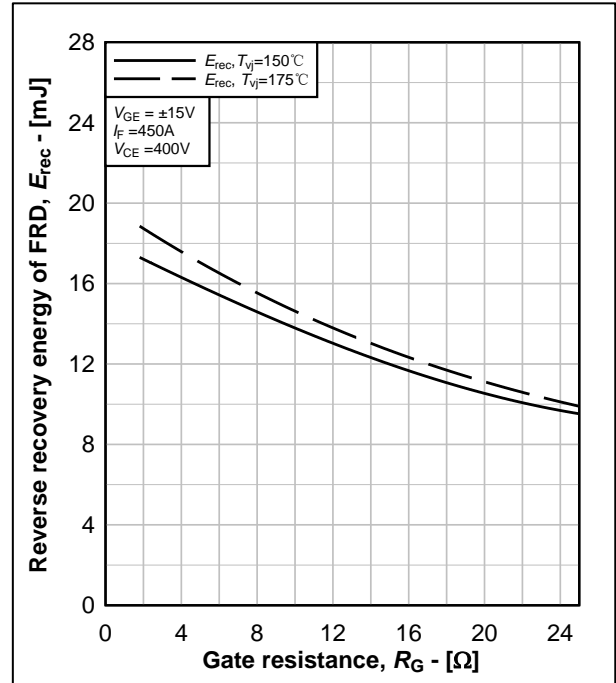


图 8. FRD 反向恢复能耗典型曲线, $E_{rec} = f(R_G)$

Fig.8 Typical FRD E_{rec} , $E_{rec} = f(R_G)$

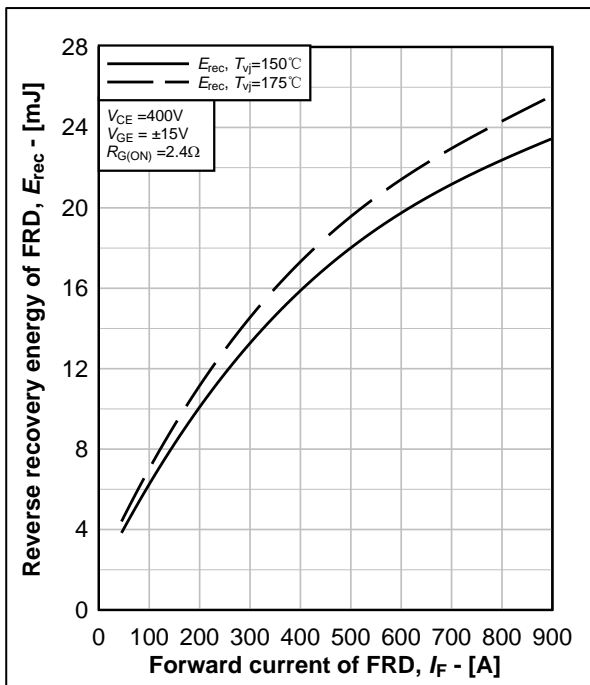


图 9. FRD 反向恢复能耗典型曲线, $E_{rec} = f(I_F)$

Fig.9 Typical FRD E_{rec} , $E_{rec} = f(I_F)$

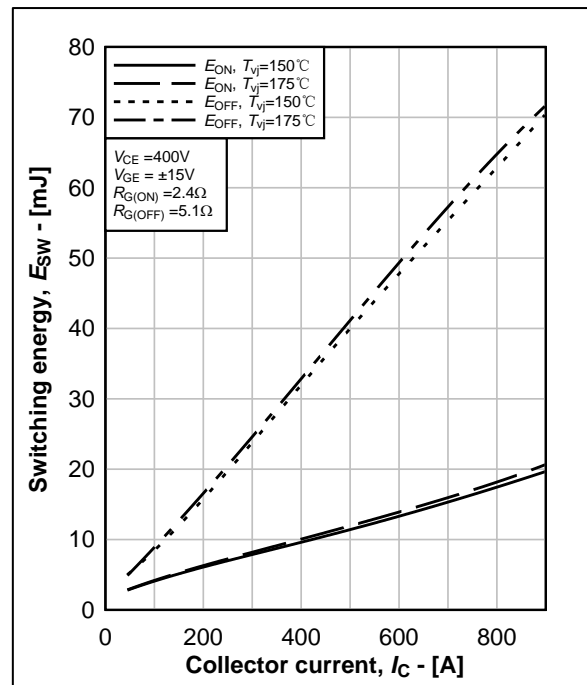


图 10. IGBT 开关能耗典型曲线, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

Fig.10 Typical IGBT switching energy, $E_{on} = f(I_C)$, $E_{off} = f(I_C)$

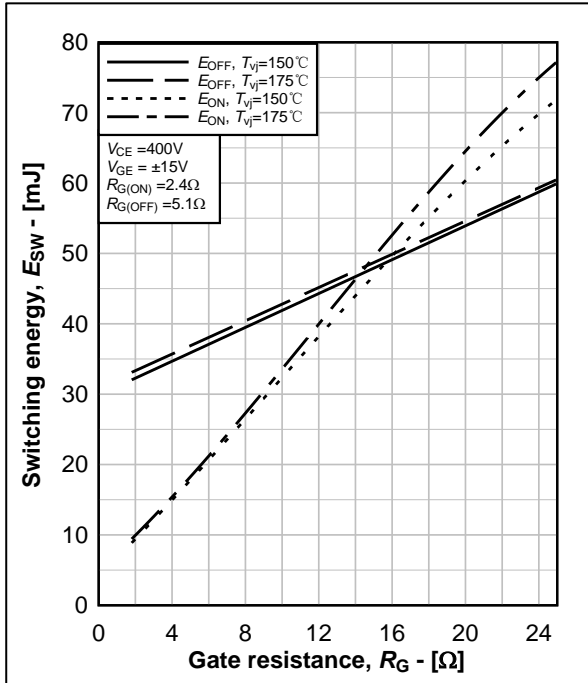

 图 11. IGBT 开关能耗典型曲线, $E_{on}=f(R_G)$, $E_{off}=f(R_G)$

Fig.11 Typical IGBT switching energy,

$$E_{on}=f(R_G), E_{off}=f(R_G)$$

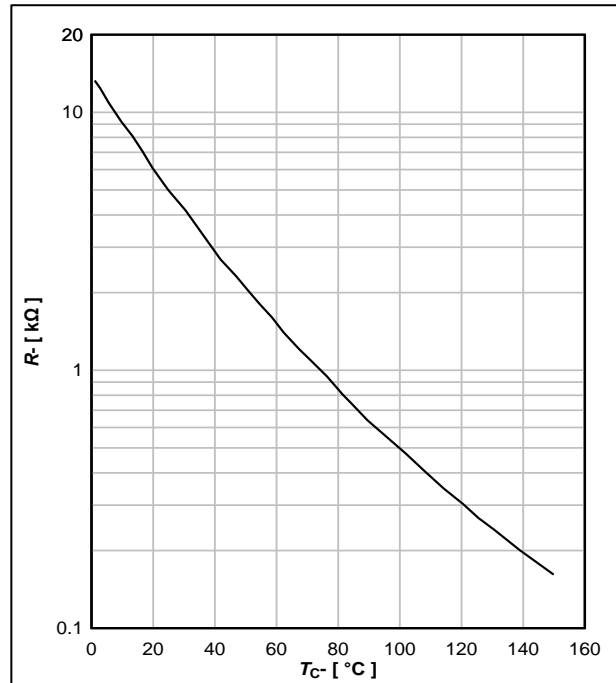

 图 12. 热敏电阻典型特性曲线, $R=f(T_C)$

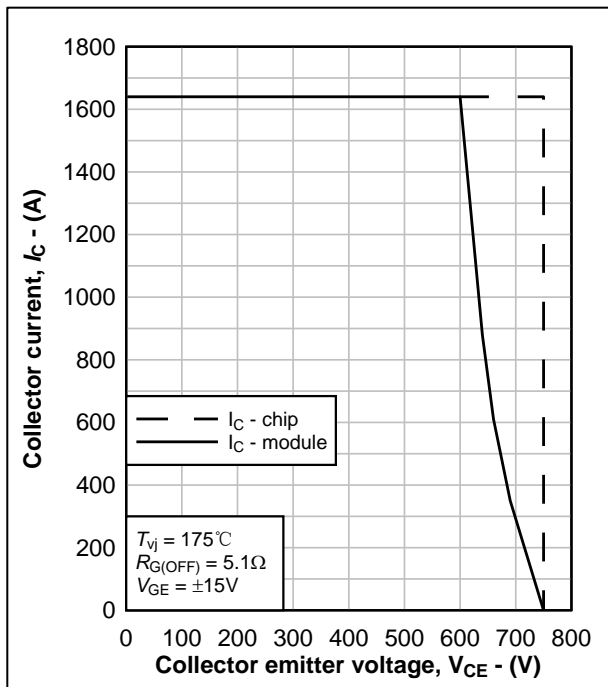
 Fig.12 Typical NTC thermistor characteristic, $R=f(T_C)$

 图 13. IGBT 反偏安全工作区, $I_C=f(V_{CE})$

Fig.13 Reverse bias safe operating area of IGBT,

$$I_C=f(V_{CE})$$

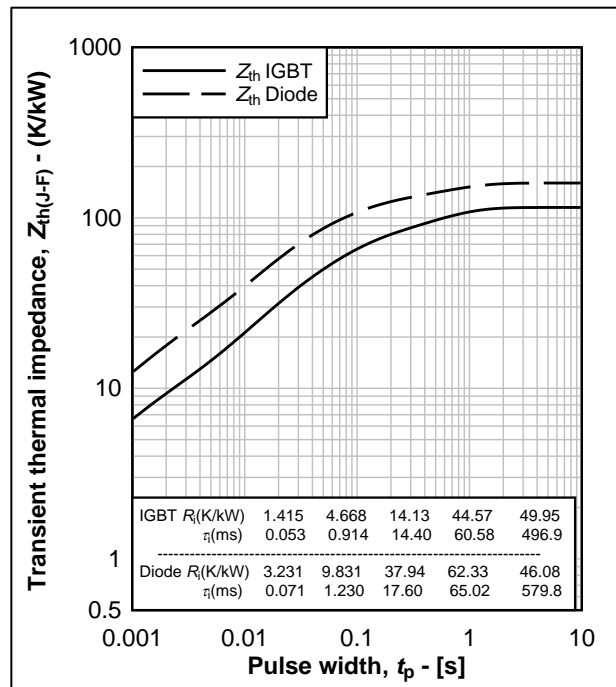
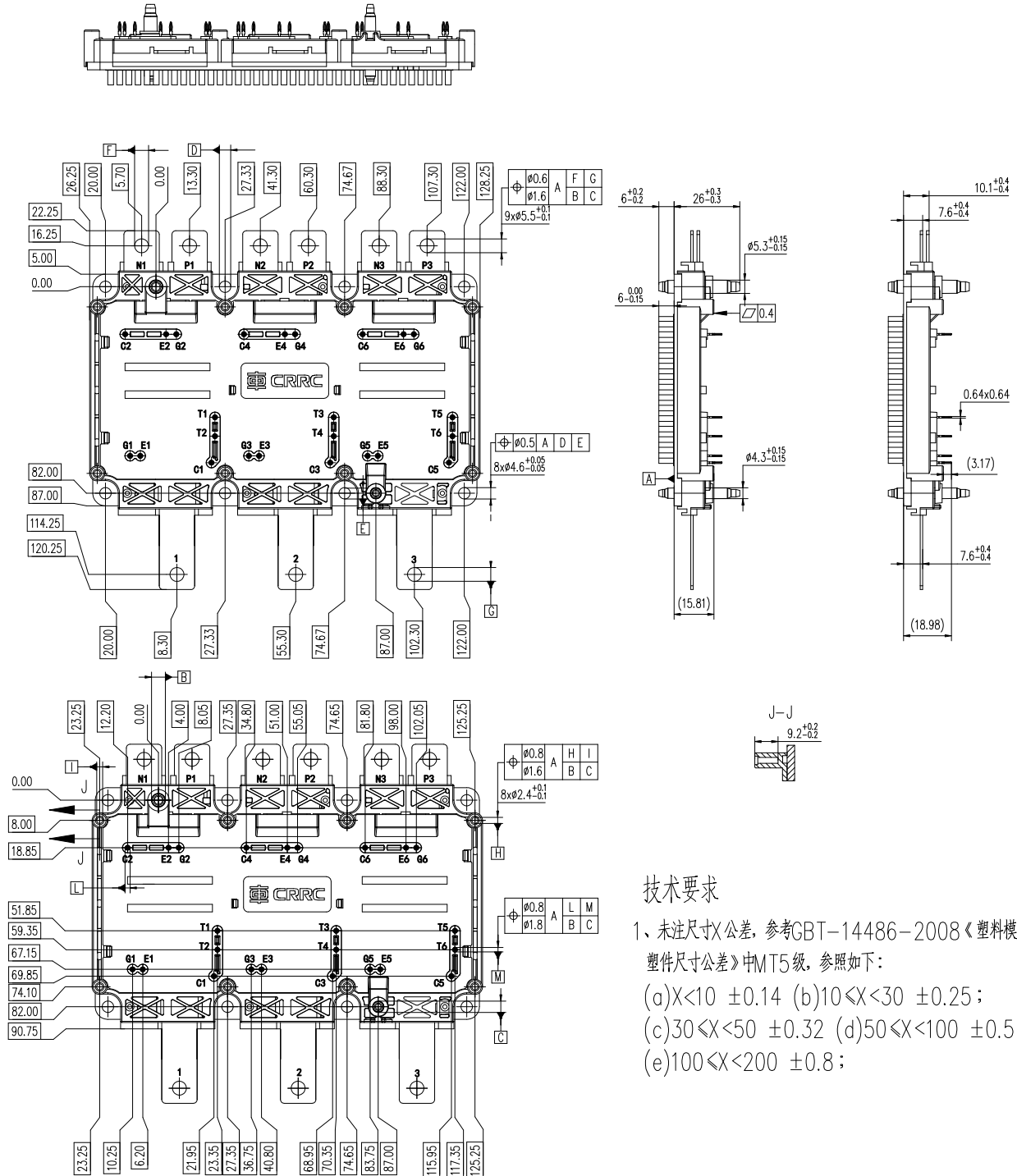

 图 14. 瞬态热阻抗曲线, $Z_{th(J-F)}=f(t_p)$

 Fig.14 Transient thermal impedance, $Z_{th(J-F)}=f(t_p)$



技术要求

- 1、未注尺寸公差，参考GB/T-14486-2008《塑料模塑件尺寸公差》中MT5级，参照如下：
- (a) $X < 10 \pm 0.14$ (b) $10 < X < 30 \pm 0.25$ ；
 (c) $30 < X < 50 \pm 0.32$ (d) $50 < X < 100 \pm 0.5$ ；
 (e) $100 < X < 200 \pm 0.8$ ；

重量 Weight: 735g 模块外观类型 Module outline code: S3

图 15. 模块外观尺寸

Fig. 15 Module outlines

株洲中车时代半导体有限公司

ZHUZHOU CRRC TIMES SEMICONDUCTOR CO., LTD.

地 址	Address	湖南省株洲市石峰区田心工业园	Tianxin Industrial Park, Shifeng District, ZhuZhou City, Hunan Province, China
邮 编	Zipcode	412001	
电 话	Telephone	+86 (0)731-28498268, 28498238, 28493472	
传 真	Fax	+86 (0)731-28498851, 28498494	
电子邮箱	Email	sbu@crzczic.cc	
网 址	Web Site	http://www.sbu.crzczic.cc	

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